

Mark: 2J

## **PNP Switching Transistor**

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	12	V
V <sub>CBO</sub>	Collector-Base Voltage	12	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
Ic	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		PN3640	*MMBT3640	
P <sub>D</sub>	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PN3640 / MMBT3640

# PNP Switching Transistor

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
/ <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	12		V
/ <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$	12		V
(BR)CBO	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	12		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 100 \ \mu A, I_{C} = 0$	4.0		V
CES	Collector Cutoff Current	$V_{CE} = 6.0 \text{ V}, V_{BE} = 0$		0.01 1.0	μΑ
В	Base Current	$V_{CE} = 6.0 \text{ V}, V_{BE} = 0, T_A = 65^{\circ}\text{C}$ $V_{CE} = 6.0 \text{ V}, V_{BE} = 0$		1.0	μA nA
,					
)N CHAR	RACTERISTICS*				
	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$	30	120	
FE		$I_{\rm C} = 50$ mA, $V_{\rm CE} = 0.0$ V	20	120	
/ <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA		0.3	V
		$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$		0.2 0.6	V V
		$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}, T_{A} = 65^{\circ}\text{C}$		0.25	v
BE(sat)	Base-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA	0.75	0.95	V
	Base-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$	0.75 0.8	0.95 1.0 1.5	V V V
/ <sub>BE(sat)</sub> SMALL SI		$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$		1.0	V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$	0.8	1.0	V V
SMALL SI T Cobo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5	MHz pF
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5	V V MHz
SMALL SI T Cobo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5	MHz pF
MALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5	MHz pF
MALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5	MHz pF
MALL SI Cobo Cibo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5 3.5	MHz pF pF
SMALL SI Cobo Cibo SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	1.0 1.5 3.5 3.5 10	MHz pF pF
SMALL SI Pobo Dibo SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5 3.5 10 30	MHz pF pF ns ns
SMALL SI r Pobo Pibo SWITCHIN d r s f	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	1.0 1.5 3.5 3.5 10 30 20	MHz pF pF ns ns ns
SMALL SI Pobo Sibo SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \end{split}$	0.8	1.0 1.5 3.5 3.5 10 30 20 12	MHz pF pF ns ns ns ns
SMALL SI Pobo Sibo SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	1.0 1.5 3.5 3.5 10 30 20 12	MHz pF pF ns ns ns ns
SMALL SI Pobo Sibo SWITCHIN	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time	$\begin{array}{c} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	1.0 1.5 3.5 3.5 10 30 20 12 25	MHz pF pF ns ns ns ns ns
SMALL SI Pobo Dibo Dibo SWITCHIN S S S S S S S S S S S S S S S S S S S	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	1.0 1.5 3.5 3.5 10 30 20 12 25	MHz pF pF ns ns ns ns ns
SMALL SI r Cobo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \hline \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ V}, \\ f = 100 \text{ MHz} \\ \hline \\ V_{CB} = 5.0 \text{ V}, I_{E} = 0, \\ f = 1.0 \text{ MHz} \\ \hline \\ V_{BE} = 0.5 \text{ V}, I_{C} = 0, \\ f = 1.0 \text{ MHz} \\ \hline \\ V_{CC} = 6.0 \text{ V}, V_{BE(off)} = 1.9 \text{ V}, \\ I_{C} = 50 \text{ mA}, I_{B1} = 5.0 \text{ mA} \\ \hline \\ V_{CC} = 6.0 \text{ V}, I_{C} = 50 \text{ mA}, \\ I_{B1} = I_{B2} = 5.0 \text{ mA} \\ \hline \\ V_{CC} = 6.0 \text{ V}, V_{BE(off)} = 1.9 \text{ V}, \\ I_{C} = 50 \text{ mA}, I_{B1} = 5.0 \text{ mA} \\ \hline \\ V_{CC} = 1.5 \text{ V}, I_{C} = 10 \text{ mA}, \\ I_{B1} = I_{B2} = 0.5 \text{ mA} \\ \hline \\ V_{CC} = 6.0 \text{ V}, V_{BE(off)} = 1.9 \text{ V}, \\ I_{C} = 50 \text{ mA}, I_{B1} = 5.0 \text{ mA} \\ \hline \end{array}$	0.8	1.0 1.5 3.5 3.5 10 30 20 12 25 60	MHz pF pF ns ns ns ns ns
SMALL SI T Cobo	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	1.0 1.5 3.5 3.5 10 30 20 12 25 60	MHz pF pF ns ns ns ns ns

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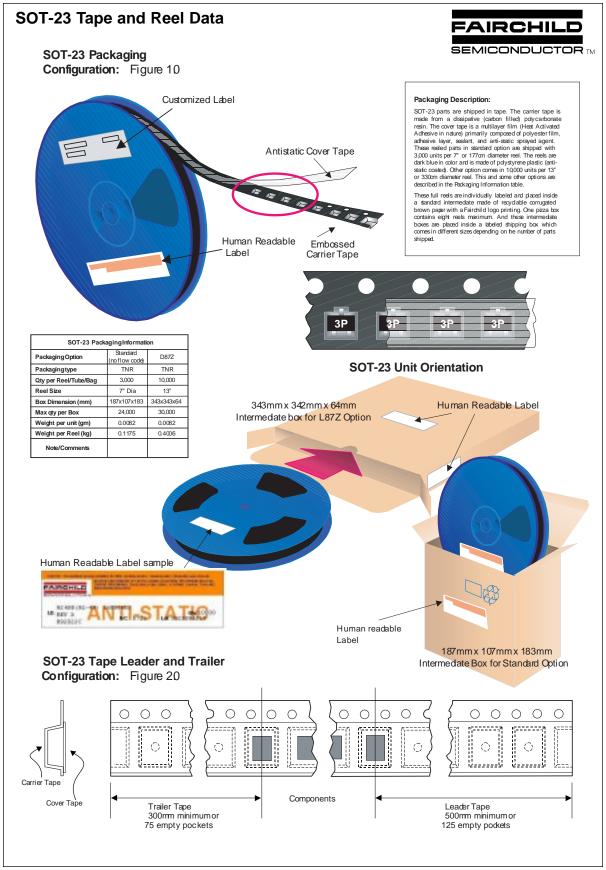
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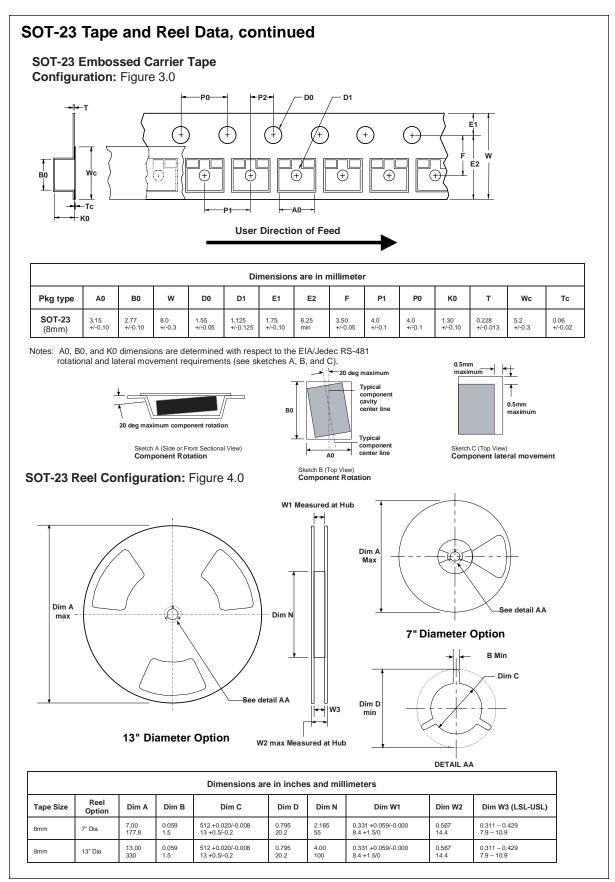
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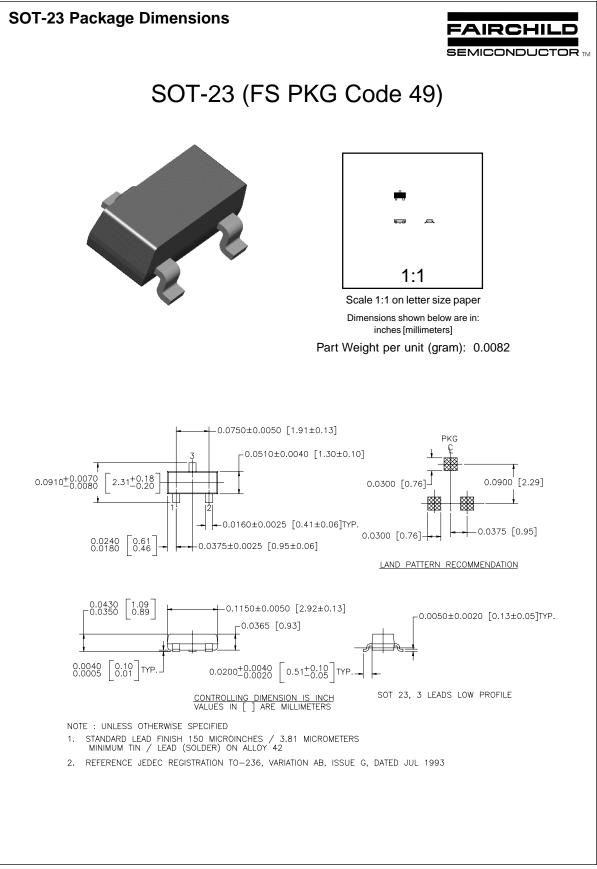


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